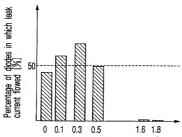


Thickness of silicon layer  $\Delta 4~[\mu\,\text{m}]$  Reverse bias: 2V (Width of depletion layer  $\Delta 3$ : 0.25 $\mu$ m)

FIG. 12



Thickness of silicon layer  $\Delta 4$  [  $\mu$  m] Reverse bias: 4V (Width of depletion layer  $\Delta 3$ : 0.4 $\mu$ m)

FIG. 13

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RE1: Leakage current when thickness of silicon layer is set at 0, 0.1, 0.3  $\mu$ m RE2: Leakage current when thickness of silicon layer is set at 0.5  $\mu$ m RE3: Leakage current in this embodiment (when thickness of silicon layer is set at 1.6, 1.8  $\mu$ m)

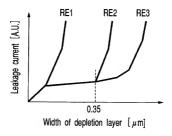


FIG. 14

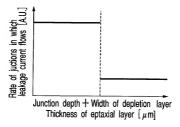
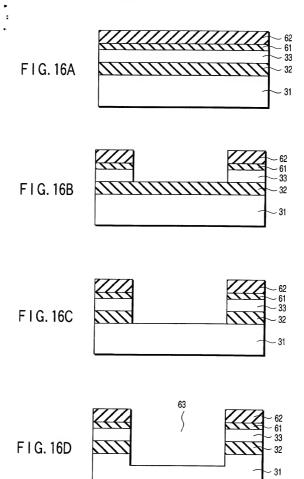
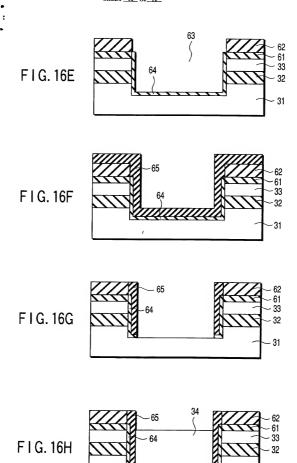


FIG. 15





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